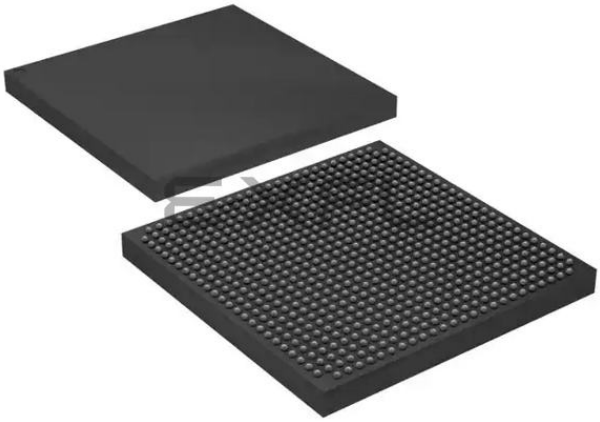
Intel - EP20K1000CF672C8 Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	3840
Number of Logic Elements/Cells	38400
Total RAM Bits	327680
Number of I/O	508
Number of Gates	1772000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k1000cf672c8

…and More Features

- Low-power operation design
  - 1.8-V supply voltage (see Table 2)
  - Copper interconnect reduces power consumption
  - MultiVolt™ I/O support for 1.8-V, 2.5-V, and 3.3-V interfaces
  - ESBs offering programmable power-saving mode
- Flexible clock management circuitry with up to four phase-locked loops (PLLs)
  - Built-in low-skew clock tree
  - Up to eight global clock signals
  - ClockLock™ feature reducing clock delay and skew
  - ClockBoost™ feature providing clock multiplication and division
  - ClockShift™ feature providing programmable clock phase and delay shifting
- Powerful I/O features
  - Compliant with peripheral component interconnect Special Interest Group (PCI SIG) ***PCI Local Bus Specification, Revision 2.2*** for 3.3-V operation at 33 or 66 MHz and 32 or 64 bits
  - Support for high-speed external memories, including DDR synchronous dynamic RAM (SDRAM) and ZBT static RAM (SRAM)
  - 16 input and 16 output LVDS channels at 840 megabits per second (Mbps)
  - Direct connection from I/O pins to local interconnect providing fast t_{CO} and t_{SU} times for complex logic
  - MultiVolt I/O support for 1.8-V, 2.5-V, and 3.3-V interfaces
  - Programmable clamp to V_{CCIO}
  - Individual tri-state output enable control for each pin
  - Programmable output slew-rate control to reduce switching noise
  - Support for advanced I/O standards, including low-voltage differential signaling (LVDS), LVPECL, PCI-X, AGP, CTT, SSTL-3 and SSTL-2, GTL+, and HSTL Class I
  - Supports hot-socketing operation
  - Pull-up on I/O pins before and during configuration

Table 2. APEX 20KC Supply Voltages

Feature	Voltage
Internal supply voltage (V_{CCINT})	1.8 V
MultiVolt I/O interface voltage levels (V_{CCIO})	1.8 V, 2.5 V, 3.3 V, 5.0 V *(1)*

Note to Table 2:
(1) APEX 20KC devices can be 5.0-V tolerant by using an external resistor.

- Advanced interconnect structure
  - Copper interconnect for high performance
  - Four-level hierarchical FastTrack® interconnect structure providing fast, predictable interconnect delays
  - Dedicated carry chain that implements arithmetic functions such as fast adders, counters, and comparators (automatically used by software tools and megafunctions)
  - Dedicated cascade chain that implements high-speed, high-fan-in logic functions (automatically used by software tools and megafunctions)
  - Interleaved local interconnect allows one LE to drive 29 other LEs through the fast local interconnect
- Advanced software support
  - Software design support and automatic place-and-route provided by the Altera® Quartus™ II development system for Windows-based PCs, Sun SPARCstations, and HP 9000 Series 700/800 workstations
  - Altera MegaCore® functions and Altera Megafunction Partners Program (AMPP℠) megafunctions optimized for APEX 20KC architecture available
  - NativeLink™ integration with popular synthesis, simulation, and timing analysis tools
  - Quartus II SignalTap® embedded logic analyzer simplifies in-system design evaluation by giving access to internal nodes during device operation
  - Supports popular revision-control software packages including PVCS, RCS, and SCCS

Table 3. APEX 20KC QFP & BGA Package Options & I/O Count *Notes (1), (2)*

Device	208-Pin PQFP	240-Pin PQFP	356-Pin BGA	652-Pin BGA
EP20K200C	136	168	271	
EP20K400C				488
EP20K600C				488
EP20K1000C				488

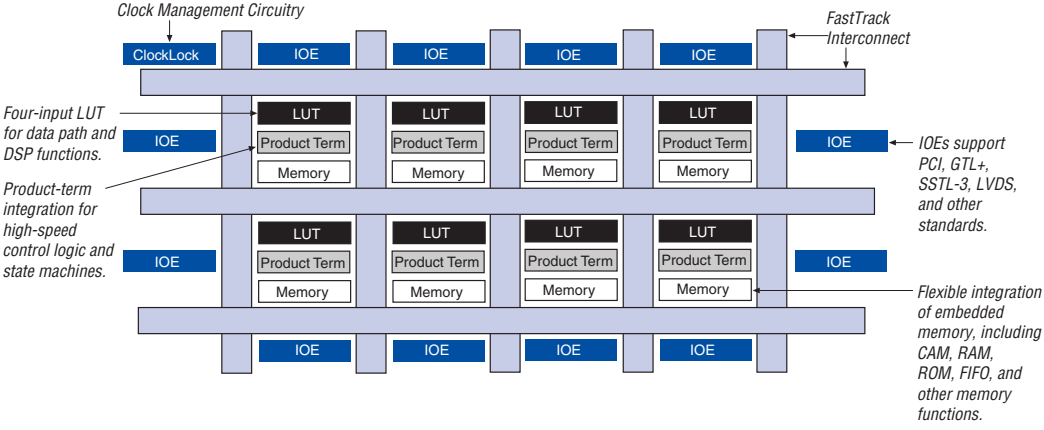
APEX 20KC devices include additional features such as enhanced I/O standard support, CAM, additional global clocks, and enhanced ClockLock clock circuitry. Table 7 shows the features included in APEX 20KC devices.

Table 7. APEX 20KC Device Features (Part 1 of 2)

Feature	APEX 20KC Devices
MultiCore system integration	Full support
Hot-socketing support	Full support
SignalTap logic analysis	Full support
32-/64-bit, 33-MHz PCI	Full compliance
32-/64-bit, 66-MHz PCI	Full compliance in -7 and -8 speed grades in selected devices
MultiVolt I/O	1.8-V, 2.5-V, or 3.3-V V_{CCIO} V_{CCIO} selected bank by bank 5.0-V tolerant with use of external resistor
ClockLock support	Clock delay reduction $m/(n \times v)$ clock multiplication Drive ClockLock output off-chip External clock feedback ClockShift circuitry LVDS support Up to four PLLs ClockShift clock phase adjustment
Dedicated clock and input pins	Eight

The ESB can implement a variety of memory functions, including CAM, RAM, dual-port RAM, ROM, and FIFO functions. Embedding the memory directly into the die improves performance and reduces die area compared to distributed-RAM implementations. Moreover, the abundance of cascadable ESBs allows APEX 20KC devices to implement multiple wide memory blocks for high-density designs. The ESB's high speed ensures it can implement small memory blocks without any speed penalty. Additionally, designers can use the ESBs to create as many different-sized memory blocks as the system requires. Figure 1 shows an overview of the APEX 20KC device.

Figure 1. APEX 20KC Device Block Diagram



APEX 20KC devices provide four dedicated clock pins and four dedicated input pins that drive register control inputs. These signals ensure efficient distribution of high-speed, low-skew control signals, which use dedicated routing channels to provide short delays and low skews. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or internally generated asynchronous clear signals with high fan-out. The dedicated clock pins featured on the APEX 20KC devices can also feed logic. The devices also feature ClockLock and ClockBoost clock management circuitry.

The counter mode uses two 3-input LUTs: one generates the counter data, and the other generates the fast carry bit. A 2-to-1 multiplexer provides synchronous loading, and another AND gate provides synchronous clearing. If the cascade function is used by an LE in counter mode, the synchronous clear or load overrides any signal carried on the cascade chain. The synchronous clear overrides the synchronous load. LEs in arithmetic mode can drive out registered and unregistered versions of the LUT output.

Clear & Preset Logic Control

Logic for the register's clear and preset signals is controlled by LAB-wide signals. The LE directly supports an asynchronous clear function. The Quartus II Compiler can use a NOT-gate push-back technique to emulate an asynchronous preset or to emulate simultaneous preset and clear or asynchronous load. However, this technique uses three additional LEs per register. All emulation is performed automatically when the design is compiled. Registers that emulate simultaneous preset and load will enter an unknown state upon power-up or when the chip-wide reset is asserted.

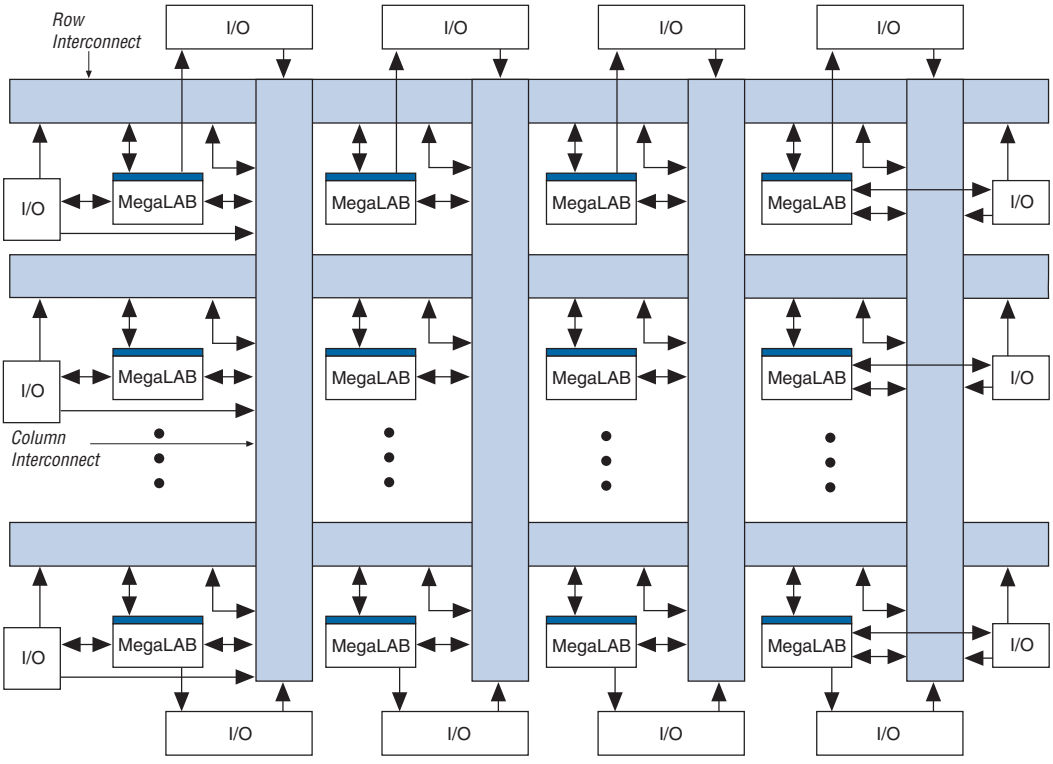
In addition to the two clear and preset modes, APEX 20KC devices provide a chip-wide reset pin (DEV_CLRn) that resets all registers in the device. Use of this pin is controlled through an option in the Quartus II software that is set before compilation. The chip-wide reset overrides all other control signals. Registers using an asynchronous preset are preset when the chip-wide reset is asserted; this effect results from the inversion technique used to implement the asynchronous preset.

FastTrack Interconnect

In the APEX 20KC architecture, connections between LEs, ESBs, and I/O pins are provided by the FastTrack interconnect. The FastTrack interconnect is a series of continuous horizontal and vertical routing channels that traverse the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack interconnect consists of row and column interconnect channels that span the entire device. The row interconnect routes signals throughout a row of MegaLAB structures; the column interconnect routes signals throughout a column of MegaLAB structures. When using the row and column interconnect, an LE, IOE, or ESB can drive any other LE, IOE, or ESB in a device. See Figure 9.

Figure 9. APEX 20KC Interconnect Structure



A row line can be driven directly by LEs, IOEs, or ESBs in that row. Further, a column line can drive a row line, allowing an LE, IOE, or ESB to drive elements in a different row via the column and row interconnect. The row interconnect drives the MegaLAB interconnect to drive LEs, IOEs, or ESBs in a particular MegaLAB structure.

A column line can be directly driven by LEs, IOEs, or ESBs in that column. A column line on a device's left or right edge can also be driven by row IOEs. The column line is used to route signals from one row to another. A column line can drive a row line; it can also drive the MegaLAB interconnect directly, allowing faster connections between rows.

Figure 10 shows how the FastTrack interconnect uses the local interconnect to drive LEs within MegaLAB structures.

ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

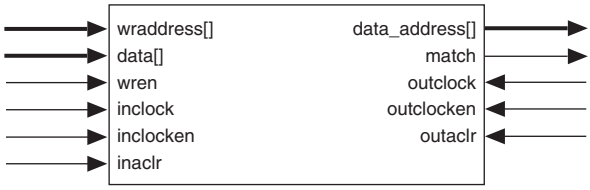
ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the FastTrack or MegaLAB interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the FastTrack and MegaLAB interconnects. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

CAM is used for high-speed search operations. When searching for data within a RAM block, the search is performed serially. Thus, finding a particular data word can take many cycles. CAM searches all addresses in parallel and outputs the address storing a particular word. When a match is found, a match flag is set high. Figure 23 shows the CAM block diagram.

Figure 23. APEX 20KC CAM Block Diagram



CAM can be used in any application requiring high-speed searches, such as networking, communications, data compression, and cache management.

The APEX 20KC on-chip CAM provides faster system performance than traditional discrete CAM. Integrating CAM and logic into the APEX 20KC device eliminates off-chip and on-chip delays, improving system performance.

When in CAM mode, the ESB implements 32-word, 32-bit CAM. Wider or deeper CAM can be implemented by combining multiple CAMs with some ancillary logic implemented in LEs. The Quartus II software combines ESBs and LEs automatically to create larger CAMs.

CAM supports writing "don't care" bits into words of the memory. The "don't care" bit can be used as a mask for CAM comparisons; any bit set to "don't care" has no effect on matches.

The output of the CAM can be encoded or unencoded. When encoded, the ESB outputs an encoded address of the data's location. For instance, if the data is located in address `12`, the ESB output is `12`. When unencoded, the ESB uses its 16 outputs to show the location of the data over two clock cycles. In this case, if the data is located in address `12`, the 12th output line goes high. When using unencoded outputs, two clock cycles are required to read the output because a 16-bit output bus is used to show the status of 32 words.

The encoded output is better suited for designs that ensure duplicate data is not written into the CAM. If duplicate data is written into two locations, the CAM's output will be incorrect. If the CAM may contain duplicate data, the unencoded output is a better solution; CAM with unencoded outputs can distinguish multiple data locations.

CAM can be pre-loaded with data during configuration, or it can be written during system operation. In most cases, two clock cycles are required to write each word into CAM. When "don't care" bits are used, a third clock cycle is required.

Implementing Logic in ROM

In addition to implementing logic with product terms, the ESB can implement logic functions when it is programmed with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of ESBs. The large capacity of ESBs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or distributed RAM blocks. Parameterized functions such as LPM functions can take advantage of the ESB automatically. Further, the Quartus II software can implement portions of a design with ESBs where appropriate.

Programmable Speed/Power Control

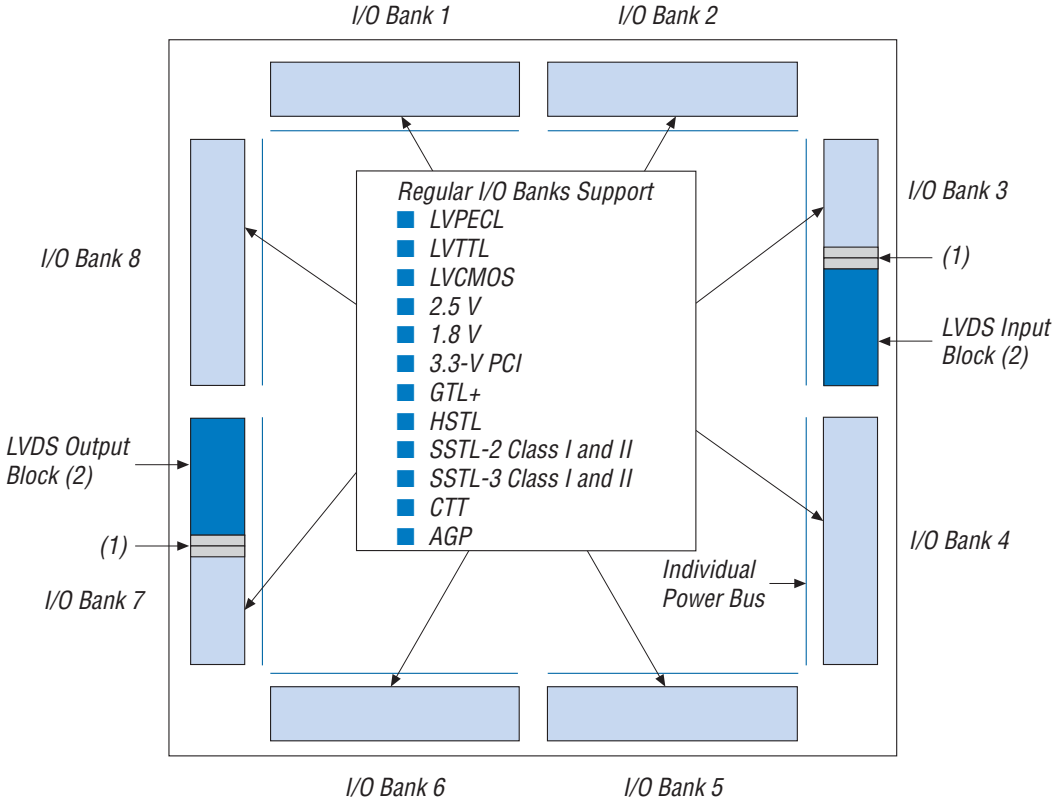
APEX 20KC ESBs offer a high-speed mode that supports very fast operation on an ESB-by-ESB basis. When high speed is not required, this feature can be turned off to reduce the ESB's power dissipation by up to 50%. ESBs that run at low power incur a nominal timing delay adder. This Turbo Bit™ option is available for ESBs that implement product-term logic or memory functions. An ESB that is not used will be powered down so that it does not consume DC current.

Designers can program each ESB in the APEX 20KC device for either high-speed or low-power operation. As a result, speed-critical paths in the design can run at high speed, while the remaining paths operate at reduced power.

I/O Structure

The APEX 20KC IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data requiring fast setup times or as an output register for data requiring fast clock-to-output performance. IOEs can be used as input, output, or bidirectional pins.

Figure 28. APEX 20KC I/O Banks



Notes to Figure 28:

(1) For more information on placing I/O pins in LVDS blocks, refer to the "Guidelines for Using LVDS Blocks" section in *Application Note 120 (Using LVDS in APEX 20KE Devices)*.

(2) If the LVDS input and output blocks are not used for LVDS, they can support all of the I/O standards and can be used as input, output, or bidirectional pins with V_{CCIO} set to 3.3 V, 2.5 V, or 1.8 V.

Power Sequencing & Hot Socketing

Because APEX 20KC devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. Therefore, the V_{CCIO} and V_{CCINT} power supplies may be powered in any order.

Tables 11 and 12 summarize the ClockLock and ClockBoost parameters for APEX 20KC devices.

Table 11. APEX 20KC ClockLock & ClockBoost Parameters *Note (1)*

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_R	Input rise time				5	ns
t_F	Input fall time				5	ns
t_{INDUTY}	Input duty cycle		40		60	%
$t_{INJITTER}$	Input jitter peak-to-peak				2% of input period	%
$t_{OUTJITTER}$	RMS jitter on ClockLock or ClockBoost-generated clock				0.35% of output period	%
$t_{OUTDUTY}$	Duty cycle for ClockLock or ClockBoost-generated clock		45		55	%
t_{LOCK} *(2), (3)*	Time required for ClockLock or ClockBoost to acquire lock				40	µs

Table 12. APEX 20KC Clock Input & Output Parameters (Part 1 of 2) *Note (1)*

Symbol	Parameter	I/O Standard	-7 Speed Grade		-8 Speed Grade		Units
			Min	Max	Min	Max	
f_{VCO} *(4)*	Voltage controlled oscillator operating range		200	500	200	500	MHz
f_{CLOCK0}	Clock0 PLL output frequency for internal use		1.5	335	1.5	200	MHz
f_{CLOCK1}	Clock1 PLL output frequency for internal use		20	335	20	200	MHz
f_{CLOCK0_EXT}	Output clock frequency for external clock0 output	3.3-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		2.5-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		1.8-V LVTTL	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		GTL+	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-2 Class I	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-2 Class II	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-3 Class I	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		SSTL-3 Class II	*(5)*	*(5)*	*(5)*	*(5)*	MHz
		LVDS	*(5)*	*(5)*	*(5)*	*(5)*	MHz

Table 18. APEX 20KC Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.375 (2.375)	2.625 (2.625)	V
	Supply voltage for output buffers, 1.8-V operation	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_I	Input voltage	*(2)*, *(5)*	–0.5	4.1	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Operating junction temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time (10% to 90%)			40	ns
t_F	Input fall time (90% to 10%)			40	ns

Table 19. APEX 20KC Device DC Operating Conditions *Notes (6), (7)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_I	Input pin leakage current *(8)*	V_I = 3.6 to 0.0 V	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current *(8)*	V_O = 4.1 to –0.5 V	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -7 speed grade		10		mA
		V_I = ground, no load, no toggling inputs, -8, -9 speed grades		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(9)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(9)*	30		80	kΩ
		V_{CCIO} = 1.71 V *(9)*	60		150	kΩ

DC operating specifications on APEX 20KC I/O standards are listed in Tables 21 to 35.

Table 28. GTL+ I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{TT}	Termination voltage		1.35	1.5	1.65	V
V_{REF}	Reference voltage		0.88	1.0	1.12	V
V_{IH}	High-level input voltage		V_{REF} + 0.1			V
V_{IL}	Low-level input voltage				V_{REF} – 0.1	V
V_{OL}	Low-level output voltage	I_{OL} = 36 mA *(2)*			0.65	V

Table 29. SSTL-2 Class I Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		2.375	2.5	2.625	V
V_{TT}	Termination voltage		V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04	V
V_{REF}	Reference voltage		1.15	1.25	1.35	V
V_{IH}	High-level input voltage		V_{REF} + 0.18		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.18	V
V_{OH}	High-level output voltage	I_{OH} = –7.6 mA *(1)*	V_{TT} + 0.57			V
V_{OL}	Low-level output voltage	I_{OL} = 7.6 mA *(2)*			V_{TT} – 0.57	V

Table 34. 3.3-V AGP I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.15	3.3	3.45	V
V_{REF}	Reference voltage		0.39 × V_{CCIO}		0.41 × V_{CCIO}	V
V_{IH}	High-level input voltage		0.5 × V_{CCIO}		V_{CCIO} + 0.5	V
V_{IL}	Low-level input voltage				0.3 × V_{CCIO}	V
V_{OH}	High-level output voltage	I_{OUT} = –500 µA	0.9 × V_{CCIO}		3.6	V
V_{OL}	Low-level output voltage	I_{OUT} = 1,500 µA			0.1 × V_{CCIO}	V
I_I	Input pin leakage current	0 < V_{IN} < V_{CCIO}	–10		10	µA

Table 35. CTT I/O Specifications

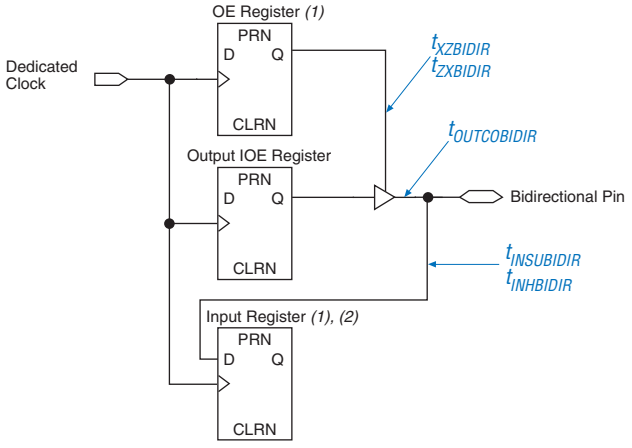
Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}/V_{REF} *(3)*	Termination and reference voltage		1.35	1.5	1.65	V
V_{IH}	High-level input voltage		V_{REF} + 0.2			V
V_{IL}	Low-level input voltage				V_{REF} – 0.2	V
I_I	Input pin leakage current	0 < V_{IN} < V_{CCIO}	–10		10	µA
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(1)*	V_{REF} + 0.4			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(2)*			V_{REF} – 0.4	V
I_O	Output leakage current (when output is high Z)	GND ≤ V_{OUT} ≤ V_{CCIO}	–10		10	µA

Notes to Tables 21 through 35:

(1) The I_{OH} parameter refers to high-level output current.
(2) The I_{OL} parameter refers to low-level output current. This parameter applies to open-drain pins as well as output pins.
(3) V_{REF} specifies center point of switching range.

Figure 31 shows the output drive characteristics of APEX 20KC devices.

Figure 35. Synchronous Bidirectional Pin External Timing



Notes to Figure 35:

(1) The output enable and input registers are LE registers in the LAB adjacent to the bidirectional pin. Use the "Output Enable Routing = Single-Pin" option in the Quartus II software to set the output enable register.

(2) Use the "Decrease Input Delay to Internal Cells = OFF" option in the Quartus II software to set the LAB-adjacent input register. This maintains a zero hold time for LAB-adjacent registers while giving a fast, position-independent setup time. Set "Decrease Input Delay to Internal Cells = ON" and move the input register farther away from the bidirectional pin for a faster setup time with zero hold time. The exact position where zero hold occurs with the minimum setup time varies with device density and speed grade.

Tables 36 to 38 describes the f_{MAX} timing parameters shown in Figure 32. Table 39 describes the functional timing parameters.

Table 36. APEX 20KC f_{MAX} LE Timing Parameters

Symbol	Parameter
t_{SU}	LE register setup time before clock
t_{H}	LE register hold time before clock
t_{CO}	LE register clock-to-output delay
t_{LUT}	LUT delay for data-in to data-out

Figure 36. AC Test Conditions for LVTTL, 2.5 V, 1.8 V, PCI & GTL+ I/O Standards

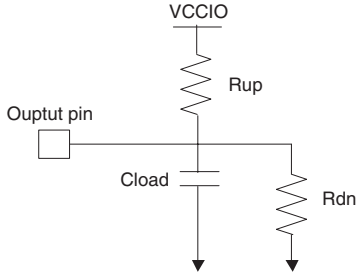


Figure 37. AC Test Conditions for SSTL-3 Class I & II I/O Standards

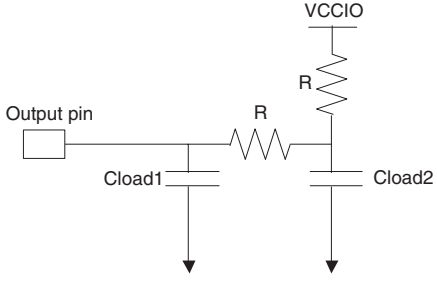
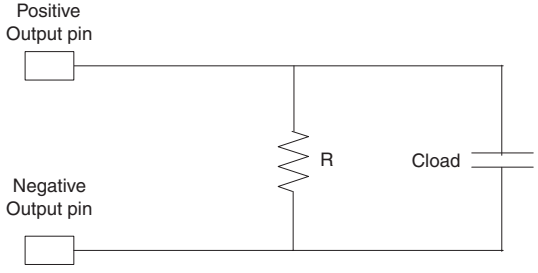


Figure 38. AC Test Conditions for the LVDS I/O Standard



Tables 44 through 67 show the f_{MAX} and external timing parameters for EPC20K200C, EP20K400C, EP20K600C, and EP20K1000C devices.

Table 44. EP20K200C f_{MAX} LE Timing Microparameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.01		0.01		0.01		ns
t_{H}	0.10		0.10		0.10		ns
t_{CO}		0.27		0.30		0.32	ns
t_{LUT}		0.65		0.78		0.92	ns

Table 45. EP20K200C f_{MAX} ESB Timing Microparameters

Symbol	-7 Speed Grade		-8 Speed Grade		-9 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.30		1.51		1.69	ns
t_{ESBSRC}		2.35		2.49		2.72	ns
t_{ESBAWC}		2.92		3.46		3.86	ns
t_{ESBSWC}		3.05		3.44		3.85	ns
$t_{ESBWASU}$	0.45		0.50		0.54		ns
t_{ESBWAH}	0.44		0.50		0.55		ns
$t_{ESBWDSU}$	0.57		0.63		0.68		ns
t_{ESBWDH}	0.44		0.50		0.55		ns
$t_{ESBRASU}$	1.25		1.43		1.56		ns
t_{ESBRAH}	0.00		0.03		0.11		ns
$t_{ESBWESU}$	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	2.01		2.27		2.45		ns
$t_{ESBWADDRSU}$	–0.20		–0.24		–0.28		ns
$t_{ESBRADDRSU}$	0.02		0.00		–0.02		ns
$t_{ESBDATACO1}$		1.09		1.28		1.43	ns
$t_{ESBDATACO2}$		2.10		2.52		2.82	ns
t_{ESBDD}		2.50		2.97		3.32	ns
t_{PD}		1.48		1.78		2.00	ns
$t_{PTERMSU}$	0.58		0.72		0.81		ns
$t_{PTERMCO}$		1.10		1.29		1.45	ns

SRAM configuration elements allow APEX 20KC devices to be reconfigured in-circuit by loading new configuration data into the device. Real-time reconfiguration is performed by forcing the device into command mode with a device pin, loading different configuration data, reinitializing the device, and resuming user-mode operation. In-field upgrades can be performed by distributing new configuration files.

Configuration Schemes

The configuration data for an APEX 20KC device can be loaded with one of five configuration schemes (see Table 70), chosen on the basis of the target application. An EPC16, EPC2, or EPC1 configuration device, intelligent controller, or the JTAG port can be used to control the configuration of an APEX 20KC device. When a configuration device is used, the system can configure automatically at system power-up.

Multiple APEX 20KC devices can be configured in any of five configuration schemes by connecting the configuration enable (nCE) and configuration enable output (nCEO) pins on each device.

Table 70. Data Sources for Configuration

Configuration Scheme	Data Source
Configuration device	EPC16, EPC8, EPC4, EPC2, or EPC1 configuration device
Passive serial (PS)	MasterBlaster or ByteBlasterMV download cable or serial data source
Passive parallel asynchronous (PPA)	Parallel data source
Passive parallel synchronous (PPS)	Parallel data source
JTAG	MasterBlaster or ByteBlasterMV download cable or a microprocessor with a Jam Standard Test and Programming Language (STAPL) or JBC File

For more information on configuration, see *Application Note 116 (Configuring SRAM-Based LUT Devices)*.

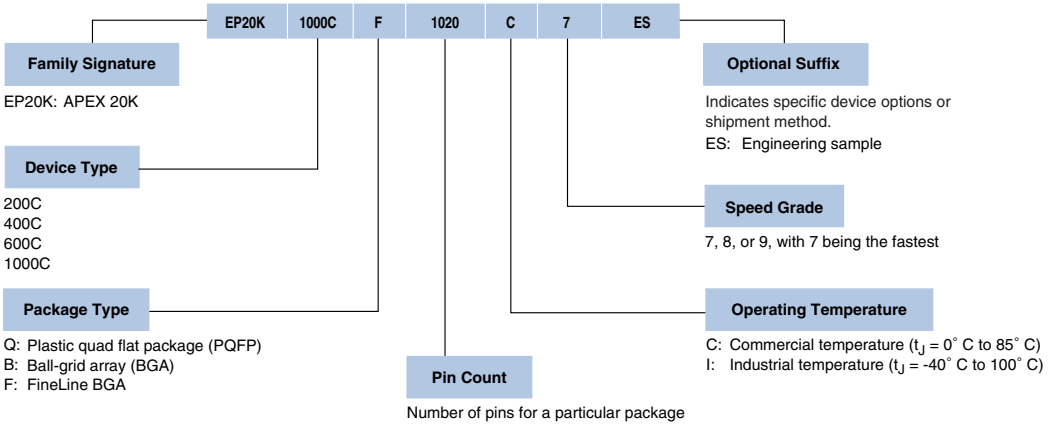
Device Pin-Outs

See the Altera web site **(http://www.altera.com)** or the ***Altera Digital Library*** for pin-out information.

Ordering Information

Figure 39 describes the ordering codes for Stratix devices. For more information on a specific package, refer to the *Altera Device Package Information Data Sheet*.

Figure 39. APEX 20KC Device Packaging Ordering Information



Revision History

The information contained in the *APEX 20KC Programmable Logic Device Data Sheet* version 2.2 supersedes information published in previous versions.

Version 2.2

The following changes were made to the *APEX 20KC Programmable Logic Device Data Sheet* version 2.2:

- Updated Tables 1.
- Updated notes in Tables 20.

Version 2.1

The following changes were made to the *APEX 20KC Programmable Logic Device Data Sheet* version 2.1:

- Removed figure on AC Test Conditions.
- Updated conditions in Tables 40 and 41.
- Added Tables 42 and 43.
- Updated V_{OD} in Table 27.
- Added Figures 36 through 38.
- Updated Tables 44 through 49.
- Updated Tables 62 through 67.
- Removed notes in Tables 44 through 67.
- Various textual changes throughout the document.